

# Shigefusa Chichibu

## List of Publications by Citations

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300  
papers

9,926  
citations

46  
h-index

92  
g-index

323  
ext. papers

10,590  
ext. citations

2.7  
avg, IF

5.66  
L-index

| #   | Paper  | IF  | Citations |
|-----|--|-----|-----------|
| 300 | Repeated temperature modulation epitaxy for p-type doping and light-emitting diode based on ZnO. <i>Nature Materials</i> , <b>2004</b> , 4, 42-46  | 27  | 1830      |
| 299 | Origin of defect-insensitive emission probability in In-containing (Al,In,Ga)N alloy semiconductors. <i>Nature Materials</i> , <b>2006</b> , 5, 810-6  | 27  | 548       |
| 298 | Effective band gap inhomogeneity and piezoelectric field in InGaN/GaN multiquantum well structures. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 2006-2008   | 3.4 | 380       |
| 297 | Blue Light-Emitting Diode Based on ZnO. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L643-L645   | 1.4 | 380       |
| 296 | Spatially resolved cathodoluminescence spectra of InGaN quantum wells. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 2346-2348  | 3.4 | 323       |
| 295 | Nonpolar and Semipolar Group III Nitride-Based Materials. <i>MRS Bulletin</i> , <b>2009</b> , 34, 304-312  | 3.2 | 217       |
| 294 | Biaxial strain dependence of exciton resonance energies in wurtzite GaN. <i>Journal of Applied Physics</i> , <b>1997</b> , 81, 417-424   | 2.5 | 215       |
| 293 | Correlation between the photoluminescence lifetime and defect density in bulk and epitaxial ZnO. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 532-534  | 3.4 | 215       |
| 292 | Exciton localization in InGaN quantum well devices. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1998</b> , 16, 2204                         |     | 205       |
| 291 | Nitrogen doped Mg <sub>x</sub> Zn <sub>1-x</sub> O/ZnO single heterostructure ultraviolet light-emitting diodes on ZnO substrates. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 013501   | 3.4 | 166       |
| 290 | Emission mechanisms of bulk GaN and InGaN quantum wells prepared by lateral epitaxial overgrowth. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 1460-1462   | 3.4 | 149       |
| 289 | Continuous-Wave Operation of m-Plane InGaN Multiple Quantum Well Laser Diodes. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, L187-L189  | 1.4 | 131       |
| 288 | Quantum-Confined Stark Effect in an AlGa <sub>x</sub> N/GaN/AlGa <sub>x</sub> N Single Quantum Well Structure. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, L914-L916  | 1.4 | 129       |
| 287 | Limiting factors of room-temperature nonradiative photoluminescence lifetime in polar and nonpolar GaN studied by time-resolved photoluminescence and slow positron annihilation techniques. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 021914 | 3.4 | 116       |
| 286 | Polarized photoreflectance spectra of excitonic polaritons in a ZnO single crystal. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 756-758  | 2.5 | 103       |
| 285 | Improvements in quantum efficiency of excitonic emissions in ZnO epilayers by the elimination of point defects. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 093505   | 2.5 | 96        |
| 284 | Radiative and nonradiative processes in strain-free Al <sub>x</sub> Ga <sub>1-x</sub> N films studied by time-resolved photoluminescence and positron annihilation techniques. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 2495-2504         | 2.5 | 82        |

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|-----|---|-----|----|
| 283 | Study of defects in GaN grown by the two-flow metalorganic chemical vapor deposition technique using monoenergetic positron beams. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 181-186  | 2.5 | 80 |
| 282 | Localized quantum well excitons in InGaN single-quantum-well amber light-emitting diodes. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 5153-5157   | 2.5 | 74 |
| 281 | Impacts of Si-doping and resultant cation vacancy formation on the luminescence dynamics for the near-band-edge emission of Al <sub>0.6</sub> Ga <sub>0.4</sub> N films grown on AlN templates by metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 213506               | 2.5 | 73 |
| 280 | Localized exciton dynamics in strained cubic In <sub>0.1</sub> Ga <sub>0.9</sub> N/GaN multiple quantum wells. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 4319-4321   | 3.4 | 72 |
| 279 | The origins and properties of intrinsic nonradiative recombination centers in wide bandgap GaN and AlGaN. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 161413   | 2.5 | 70 |
| 278 | Prospective emission efficiency and in-plane light polarization of nonpolar m-plane In <sub>x</sub> Ga <sub>1-x</sub> N/GaN blue light emitting diodes fabricated on freestanding GaN substrates. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 091906   | 3.4 | 67 |
| 277 | Layer-by-layer growth of high-optical-quality ZnO film on atomically smooth and lattice relaxed ZnO buffer layer. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 2784-2786  | 3.4 | 66 |
| 276 | Optical and structural studies in InGaN quantum well structure laser diodes. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2001</b> , 19, 2177   |     | 66 |
| 275 | Exciton spectra of an AlN epitaxial film on (0001) sapphire substrate grown by low-pressure metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 652-654  | 3.4 | 63 |
| 274 | Helicon-wave-excited-plasma sputtering epitaxy of ZnO on sapphire (0001) substrates. <i>Journal of Applied Physics</i> , <b>2002</b> , 91, 874-877  | 2.5 | 62 |
| 273 | Exciton-polariton spectra and limiting factors for the room-temperature photoluminescence efficiency in ZnO. <i>Semiconductor Science and Technology</i> , <b>2005</b> , 20, S67-S77  | 1.8 | 61 |
| 272 | Relation between Al vacancies and deep emission bands in AlN epitaxial films grown by NH <sub>3</sub> -source molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 241914   | 3.4 | 60 |
| 271 | Exciton Spectra of Cubic and Hexagonal GaN Epitaxial Films. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 1976-1983  | 1.4 | 59 |
| 270 | Extremely high quantum efficiency of donor-acceptor-pair emission in N-and-B-doped 6H-SiC. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 093108   | 2.5 | 59 |
| 269 | Time-resolved photoluminescence, positron annihilation, and Al <sub>0.23</sub> Ga <sub>0.77</sub> N/GaN heterostructure growth studies on low defect density polar and nonpolar freestanding GaN substrates grown by hydride vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 103518 | 2.5 | 56 |
| 268 | Vacancy-oxygen complexes and their optical properties in AlN epitaxial films studied by positron annihilation. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 054501  | 2.5 | 54 |
| 267 | Visible and Ultraviolet Photoluminescence from Cu <sub>2</sub> Te <sub>12</sub> Chalcopyrite Semiconductors Grown by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 1703-1714   | 1.4 | 54 |
| 266 | Photoreflectance spectra of a ZnO heteroepitaxial film on the nearly lattice-matched ScAlMgO <sub>4</sub> (0001) substrate grown by laser molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 2860-2862  | 3.4 | 52 |

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| 265 | Cathodoluminescence characterization of dislocations in gallium nitride using a transmission electron microscope. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 4315-4319  | 2.5 | 51 |
| 264 | Evidence of localization effects in InGaN single-quantum-well ultraviolet light-emitting diodes. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 1671-1673  | 3.4 | 51 |
| 263 | Radiative and nonradiative excitonic transitions in nonpolar (112 0) and polar (0001 ) and (0001) ZnO epilayers. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 1079-1081  | 3.4 | 50 |
| 262 | Improved quantum efficiency in nonpolar (112 0) AlGaIn/GaN quantum wells grown on GaN prepared by lateral epitaxial overgrowth. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 3768-3770   | 3.4 | 50 |
| 261 | Localized exciton dynamics in nonpolar (1120) InxGa1-xN multiple quantum wells grown on GaN templates prepared by lateral epitaxial overgrowth. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 151918  | 3.4 | 50 |
| 260 | High temperature growth of ZnS films on bare Si and transformation of ZnS to ZnO by thermal oxidation. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 616-618  | 3.4 | 50 |
| 259 | Impact of growth polar direction on the optical properties of GaN grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 28-30  | 3.4 | 50 |
| 258 | Nitrogen vacancies as a common element of the green luminescence and nonradiative recombination centers in Mg-implanted GaN layers formed on a GaN substrate. <i>Applied Physics Express</i> , <b>2017</b> , 10, 061002  | 2.4 | 49 |
| 257 | Ammonothermal Crystal Growth of GaN Using an NH4F Mineralizer. <i>Crystal Growth and Design</i> , <b>2013</b> , 13, 4158-4161  | 3.5 | 48 |
| 256 | Analysis of MBE growth mode for GaN epilayers by RHEED. <i>Journal of Crystal Growth</i> , <b>1998</b> , 189-190, 364-369  | 1.6 | 48 |
| 255 | Structural, elastic, and polarization parameters and band structures of wurtzite ZnO and MgO. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 073503  | 2.5 | 46 |
| 254 | Free and bound exciton fine structures in AlN epilayers grown by low-pressure metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 023529  | 2.5 | 44 |
| 253 | Plasma-assisted Molecular Beam Epitaxy of High Optical Quality MgZnO Films on Zn-polar ZnO Substrates. <i>Applied Physics Express</i> , <b>2008</b> , 1, 091202  | 2.4 | 44 |
| 252 | Fabrication of Visible-Light-Transparent Solar Cells Using p-Type NiO Films by Low Oxygen Fraction Reactive RF Sputtering Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 021102  | 1.4 | 42 |
| 251 | Photoreflectance spectra of excitonic polaritons in GaN substrate prepared by lateral epitaxial overgrowth. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 1576-1578   | 3.4 | 42 |
| 250 | Photoreflectance of Cu-based III/II2 heteroepitaxial layers grown by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>1996</b> , 79, 2043-2054   | 2.5 | 42 |
| 249 | Recombination dynamics of localized excitons in cubic InxGa1-xN/GaN multiple quantum wells grown by radio frequency molecular beam epitaxy on 3C-BiC substrate. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2003</b> , 21, 1856 |     | 41 |
| 248 | Impact of strain on free-exciton resonance energies in wurtzite AlN. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 123707   | 2.5 | 40 |

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| 247 | Carrier Trapping by Vacancy-Type Defects in Mg-Implanted GaN Studied Using Monoenergetic Positron Beams. <i>Physica Status Solidi (B): Basic Research</i> , <b>2018</b> , 255, 1700521   | 1.3 | 39 |
| 246 | Quantum-confined Stark effects in the m-plane In <sub>0.15</sub> Ga <sub>0.85</sub> N/GaN multiple quantum well blue light-emitting diode fabricated on low defect density freestanding GaN substrate. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 181903 | 3.4 | 39 |
| 245 | Growth of AlGaIn nanowires by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 183108  | 3.4 | 39 |
| 244 | Use of diethylselenide as a less-hazardous source for preparation of CuInSe <sub>2</sub> photo-absorbers by selenization of metal precursors. <i>Journal of Crystal Growth</i> , <b>2002</b> , 243, 404-409  | 1.6 | 37 |
| 243 | Direct correlation between the internal quantum efficiency and photoluminescence lifetime in undoped ZnO epilayers grown on Zn-polar ZnO substrates by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 063502     | 2.5 | 36 |
| 242 | Dielectric SiO <sub>2</sub> /rO <sub>2</sub> distributed Bragg reflectors for ZnO microcavities prepared by the reactive helicon-wave-excited-plasma sputtering method. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 161914                                | 3.4 | 36 |
| 241 | Band-edge photoluminescence of CuGaSe <sub>2</sub> films grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>1996</b> , 79, 4318   | 2.5 | 35 |
| 240 | Large electron capture-cross-section of the major nonradiative recombination centers in Mg-doped GaN epilayers grown on a GaN substrate. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 211901  | 3.4 | 35 |
| 239 | Optical properties of nearly stacking-fault-free m-plane GaN homoepitaxial films grown by metal organic vapor phase epitaxy on low defect density freestanding GaN substrates. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 091912                         | 3.4 | 34 |
| 238 | Experimental determination of band offsets of NiO-based thin film heterojunctions. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 163108   | 2.5 | 33 |
| 237 | Optical Properties of InGaIn/GaN Quantum Wells with Si Doped Barriers. <i>Japanese Journal of Applied Physics</i> , <b>1998</b> , 37, L1362-L1364  | 1.4 | 33 |
| 236 | Greenish-white electroluminescence from p-type CuGaS <sub>2</sub> heterojunction diodes using n-type ZnO as an electron injector. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 4403  | 3.4 | 31 |
| 235 | Defect-Resistant Radiative Performance of m-Plane Immiscible Al In N Epitaxial Nanostructures for Deep-Ultraviolet and Visible Polarized Light Emitters. <i>Advanced Materials</i> , <b>2017</b> , 29, 1603644   | 2.4 | 30 |
| 234 | Reduced defect densities in the ZnO epilayer grown on Si substrates by laser-assisted molecular-beam epitaxy using a ZnS epitaxial buffer layer. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 5586-5588  | 3.4 | 30 |
| 233 | Room-temperature near-band-edge photoluminescence from CuInSe <sub>2</sub> heteroepitaxial layers grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 1840-1842  | 3.4 | 29 |
| 232 | Excitonic photoluminescence in a CuAlSe <sub>2</sub> chalcopyrite semiconductor grown by low-pressure metalorganic chemical-vapor deposition. <i>Journal of Applied Physics</i> , <b>1993</b> , 74, 6446-6447  | 2.5 | 29 |
| 231 | Defect characterization in Mg-doped GaN studied using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 014508   | 2.5 | 28 |
| 230 | Microstructural evolution in m-plane GaN growth on m-plane SiC. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 0511124   | 3.4 | 28 |

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| 229 | Investigation of direct and indirect band gaps of [100]-oriented nearly strain-free $\Gamma$ -FeSi <sub>2</sub> films grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 556-558                                      | 3.4  | 28 |
| 228 | Carrier localization structure combined with current micropaths in AlGa <sub>N</sub> quantum wells grown on an AlN template with macrosteps. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 011102  | 3.4  | 28 |
| 227 | Photoluminescence of CuGaS <sub>2</sub> epitaxial layers grown by metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 3793-3799  | 2.5  | 27 |
| 226 | Major impacts of point defects and impurities on the carrier recombination dynamics in AlN. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 201904  | 3.4  | 26 |
| 225 | Improved characteristics and issues of m-plane InGa <sub>N</sub> films grown on low defect density m-plane freestanding GaN substrates by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 151908                  | 3.4  | 26 |
| 224 | Room-temperature photoluminescence lifetime for the near-band-edge emission of (000 1 $\bar{1}$ ) p-type GaN fabricated by sequential ion-implantation of Mg and H. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 191901                         | 3.4  | 26 |
| 223 | V defects of ZnO thin films grown on Si as an ultraviolet optical path. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 502-504   | 3.4  | 25 |
| 222 | Identification of extremely radiative nature of AlN by time-resolved photoluminescence. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 061906  | 3.4  | 24 |
| 221 | Origin of localized excitons in In-containing three-dimensional bulk (Al,In,Ga)N alloy films probed by time-resolved photoluminescence and monoenergetic positron annihilation techniques. <i>Philosophical Magazine</i> , <b>2007</b> , 87, 2019-2039 | 1.6  | 24 |
| 220 | An attenuated-total-reflection study on the surface phonon-polariton in GaN. <i>Journal of Physics Condensed Matter</i> , <b>2000</b> , 12, 7041-7044  | 1.8  | 24 |
| 219 | Photoreflectance Study of CuAlSe <sub>2</sub> Heteroepitaxial Layers. <i>Japanese Journal of Applied Physics</i> , <b>1993</b> , 32, L167-L169   | 1.4  | 24 |
| 218 | Determination of absolute value of quantum efficiency of radiation in high quality GaN single crystals using an integrating sphere. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 015704  | 2.5  | 24 |
| 217 | Collateral evidence for an excellent radiative performance of Al <sub>x</sub> Ga <sub>1-x</sub> N alloy films of high AlN mole fractions. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 051902  | 3.4  | 23 |
| 216 | Electroreflectance of CuInSe <sub>2</sub> Single Crystals. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, L543-L546  | 1.4  | 23 |
| 215 | Optical and electrical properties of AgIn(SSe) <sub>2</sub> crystals. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 302-303, 349-356  | 3.4  | 23 |
| 214 | Experimental Determination of Valence Band Discontinuities at Cu(Al,Ga)(S,Se) <sub>2</sub> /GaAs(001) Heterointerfaces Using Ultraviolet Photoemission Spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, L428-L430          | 1.4  | 23 |
| 213 | A Low-Symmetry Cubic Mesophase of Dendronized CdS Nanoparticles and Their Structure-Dependent Photoluminescence. <i>CheM</i> , <b>2017</b> , 2, 860-876  | 16.2 | 22 |
| 212 | Anisotropic optical gain in m-plane In <sub>x</sub> Ga <sub>1-x</sub> N/GaN multiple quantum well laser diode wafers fabricated on the low defect density freestanding GaN substrates. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 091112       | 3.4  | 22 |

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| 211 | Improvement of Al-Polar AlN Layer Quality by Three-Stage Flow-Modulation Metalorganic Chemical Vapor Deposition. <i>Applied Physics Express</i> , <b>2008</b> , 1, 021102  | 2.4 | 22 |
| 210 | Fabrication of p-CuGaS <sub>2</sub> /n-ZnO:Al heterojunction light-emitting diode grown by metalorganic vapor phase epitaxy and helicon-wave-excited-plasma sputtering methods. <i>Journal of Physics and Chemistry of Solids</i> , <b>2005</b> , 66, 1868-1871                      | 3.9 | 22 |
| 209 | Excitonic emission dynamics in homoepitaxial AlN films studied using polarized and spatio-time-resolved cathodoluminescence measurements. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 142103   | 3.4 | 21 |
| 208 | Reduction in the concentration of cation vacancies by proper Si-doping in the well layers of high AlN mole fraction Al <sub>x</sub> Ga <sub>1-x</sub> N multiple quantum wells grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 121602 | 3.4 | 21 |
| 207 | Radiative and nonradiative lifetimes in nonpolar m-plane In <sub>x</sub> Ga <sub>1-x</sub> N/GaN multiple quantum wells grown on GaN templates prepared by lateral epitaxial overgrowth. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2007</b> , 25, 1524                |     | 21 |
| 206 | Ultraviolet photoluminescence from CuAlS <sub>2</sub> heteroepitaxial layers grown by low-pressure metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 3513-3515  | 3.4 | 21 |
| 205 | Heteroepitaxial Growth of CuGaS <sub>2</sub> Layers by Low-Pressure Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1995</b> , 34, 3991-3997   | 1.4 | 21 |
| 204 | Effects of controlled As pressure annealing on deep levels of liquid-encapsulated Czochralski GaAs single crystals. <i>Journal of Applied Physics</i> , <b>1988</b> , 64, 3987-3993  | 2.5 | 21 |
| 203 | Thermal stability of semi-insulating property of Fe-doped GaN bulk films studied by photoluminescence and monoenergetic positron annihilation techniques. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 083542  | 2.5 | 20 |
| 202 | Importance of lattice matching and surface arrangement for the helicon-wave-excited-plasma sputtering epitaxy of ZnO. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 7856-7861  | 2.5 | 20 |
| 201 | Localized excitons in an In <sub>0.06</sub> Ga <sub>0.94</sub> N multiple-quantum-well laser diode lased at 400 nm. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 341-343   | 3.4 | 20 |
| 200 | Raman scattering from phonon-polaritons in GaN. <i>Physical Review B</i> , <b>2000</b> , 62, 10861-10866   | 3.3 | 20 |
| 199 | Photoreflectance and Photoluminescence Studies of CuAl <sub>x</sub> Ga <sub>1-x</sub> Se <sub>2</sub> Alloys. <i>Japanese Journal of Applied Physics</i> , <b>1993</b> , 32, L1304-L1307   | 1.4 | 20 |
| 198 | Low-resistivity m-plane freestanding GaN substrate with very low point-defect concentrations grown by hydride vapor phase epitaxy on a GaN seed crystal synthesized by the ammonothermal method. <i>Applied Physics Express</i> , <b>2015</b> , 8, 095501                            | 2.4 | 19 |
| 197 | Surface stoichiometry and activity control for atomically smooth low dislocation density ZnO and pseudomorphic MgZnO epitaxy on a Zn-polar ZnO substrate by the helicon-wave-excited-plasma sputtering epitaxy method. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 063541 | 2.5 | 19 |
| 196 | Recombination dynamics of excitons in Mg <sub>0.11</sub> Zn <sub>0.89</sub> O alloy films grown using the high-temperature-annealed self-buffer layer by laser-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 141903                            | 3.4 | 19 |
| 195 | Metalorganic vapor phase epitaxy of Cu(Al <sub>x</sub> Ga <sub>1-x</sub> )(SySe <sub>1-y</sub> ) <sub>2</sub> chalcopyrite semiconductors and their band offsets. <i>Journal of Physics and Chemistry of Solids</i> , <b>2003</b> , 64, 1481-1489                                    | 3.9 | 19 |
| 194 | Exciton-exciton interaction and heterobiexcitons in GaN. <i>Physical Review B</i> , <b>2003</b> , 67,  | 3.3 | 19 |

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|-----|---|-----|----|
| 193 | Observation of Exciton-Polariton Emissions from a ZnO Epitaxial Film on the a-Face of Sapphire Grown by Radical-Source Molecular-Beam-Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, L935-L937   | 1.4 | 19 |
| 192 | Internal quantum efficiency of radiation in a bulk CH <sub>3</sub> NH <sub>3</sub> PbBr <sub>3</sub> perovskite crystal quantified by using the omnidirectional photoluminescence spectroscopy. <i>APL Materials</i> , <b>2019</b> , 7, 071116                                    | 5.7 | 18 |
| 191 | High internal quantum efficiency ultraviolet to green luminescence peaks from pseudomorphic m-plane Al <sub>1-x</sub> In <sub>x</sub> N epilayers grown on a low defect density m-plane freestanding GaN substrate. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 213501 | 2.5 | 18 |
| 190 | Direct comparison of photoluminescence lifetime and defect densities in ZnO epilayers studied by time-resolved photoluminescence and slow positron annihilation techniques. <i>Physica Status Solidi A</i> , <b>2004</b> , 201, 2841-2845   |     | 18 |
| 189 | Optical nonlinearities and phase relaxation of excitons in GaN. <i>Physical Review B</i> , <b>2002</b> , 65,  | 3.3 | 18 |
| 188 | Vacancies and electron trapping centers in acidic ammonothermal GaN probed by a monoenergetic positron beam. <i>Journal of Crystal Growth</i> , <b>2016</b> , 448, 117-121  | 1.6 | 17 |
| 187 | Growth and doping characteristics of ZnSeTe epilayers by MOCVD. <i>Journal of Crystal Growth</i> , <b>1997</b> , 170, 518-522   | 1.6 | 17 |
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